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(54) **SEMICONDUCTOR APPARATUS HAVING
MULTI-LAYERED BIT LINE CONTACT AND
MANUFACTURING METHOD OF THE SAME**

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(57) **ABSTRACT**

A semiconductor device includes a substrate that includes an element separation film, an active region defined by the element separation film and arranged in a first direction, and a trench positioned across the active region and the element separation film, a bit line contact that is positioned within the trench and is connected to the active region, a bit line structure that is connected to the substrate through the bit line contact and that extends in a second direction different from the first direction across the active region, and a first contact spacer, a second contact spacer, and a third contact spacer within the trench and around the bit line contact, the first contact spacer being continuous within the trench, and each of the second contact spacer and the third contact spacer being separated into at least two discrete parts within the trench.

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